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8-16-02  
MOLIN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Patent Application of

Yukiyasu SUGANO et al.

Serial No. 09/478,812

Filed: January 7, 2000

For: Process For Producing Thin  
Film Semiconductor Device and  
Laser Irradiation Apparatus

Group Art Unit: 2815

Examiner: E. Lee

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AUG 12 2002  
TECHNOLOGY CENTER 2800

AMENDMENTCommissioner of Patents  
Washington, DC 20231

Sir:

In response to the Official Action mailed April 8, 2002,  
please amend the application as follows.

IN THE CLAIMS:

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C  
B'*

11. (amended) A thin film semiconductor device comprising a semiconductor thin film, a gate insulating film accumulated on one surface thereof, and a gate electrode accumulated entirely within a prescribed region of said semiconductor thin film through said gate insulating thin film,

wherein said semiconductor thin film is formed by forming a 30 to 80 nm layer of amorphous silicon or polycrystalline silicon having a first particle diameter on a substrate, and irradiating said substrate with an energy beam to convert said semiconductor thin film to polycrystalline silicon having a